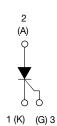
VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

High Voltage Phase Control Thyristor, 16 A





3L TO-220 FullPAK

PRIMARY CHARACTERISTICS				
I _{T(AV)} 10 A				
V _{DRM} /V _{RRM}	800 V, 1200 V			
V_{TM}	1.4 V			
I _{GT}	60 mA			
T _J	-40 °C to 125 °C			
Package	3L TO-220 FullPAK			
Circuit configuration	Single SCR			

FEATURES

- · Designed and qualified for industrial level
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL pending
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	10	^		
I _{RMS}		16	A		
V _{DRM} /V _{RRM}		800, 1200	V		
I _{TSM}		200	A		
V _T	10 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
T,I	Range	-40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-16TTS08FP-M3	800	800	10			
VS-16TTS12FP-M3	1200	1200	10			



VS-16TTS08FP-M3, VS-16TTS12FP-M3

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PARAMETER	STINIBUL		TEST CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 70 ^{\circ}{\rm C}, 1$	80° conduction, half sine wave	1	0	
Maximum RMS on-state current	I _{RMS}			1	6	Α
Maximum peak, one-cycle,	I	10 ms sine p	ulse, rated V _{RRM} applied	1	70	A
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	2	00	
Maximum I ² t for fusing	l ² t	10 ms sine p	ulse, rated V _{RRM} applied	14	44	A ² s
Maximum 1-t for fusing	1-1	10 ms sine p	10 ms sine pulse, no voltage reapplied		00	7 A ² S
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		000	A²√s
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25	10 A, T _J = 25 °C		.4	٧
On-state slope resistance	r _t	T _{.1} = 125 °C		24	1.0	mΩ
Threshold voltage	V _{T(TO)}	1j=125 C	I _J = 125 °C		.1	V
Maximum rayaraa and direct lookage current	1 /1	T _J = 25 °C	V - Reted V A	0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$V_R = Rated V_{RRM}/V_{DRM}$		1	0	
Holding current	l _H	Anode supply = 6 V, resistive load, initial I_T = 1 A 16TTS08FP, 16TTS12FP, T_J = 25 °C		-	150	mA
Maximum latching current	IL	Anode supply = 6 V, resistive load, T _J = 25 °C 200		00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		00	V/µs	
Maximum rate of rise of turned-on current	dI/dt			1:	50	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0] vv
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
	I _{GT}	Anode supply = 6 V, resistive load, T _J = -10 °C	90	mA
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	60	
		Anode supply = 6 V, resistive load, T _J = 125 °C	35	
		Anode supply = 6 V, resistive load, T_J = -10 $^{\circ}$ C	3.0	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = 25$ °C	2.0	V
Tollage to allege.		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	\ \
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Peted value	0.25	
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T. = 195 °C	4	μs
Typical turn-off time	tq	T _J = 125 °C	110	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf · in)
		Case style 3L TO-220 FullPAK	16TTS	08FP	
Marking device				16TTS	12FP

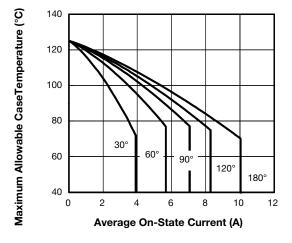


Fig. 1 - Current Rating Characteristics

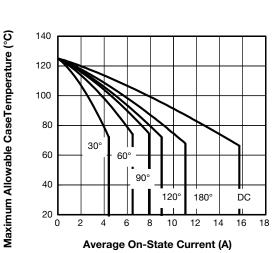


Fig. 2 - Current Rating Characteristics

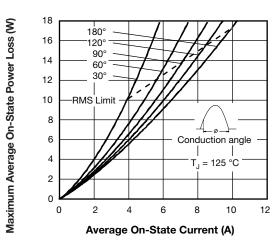


Fig. 3 - On-State Power Loss Characteristics

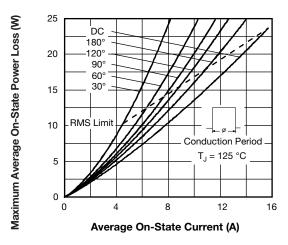
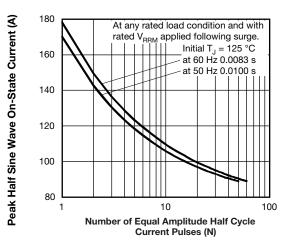


Fig. 4 - On-State Power Loss Characteristics



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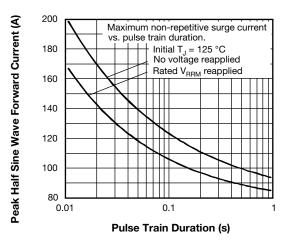


Fig. 6 - Maximum Non-Repetitive Surge Current

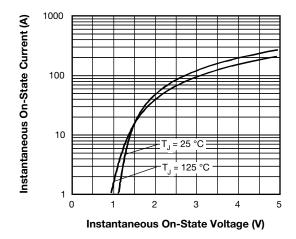


Fig. 7 - On-State Voltage Drop Characteristics

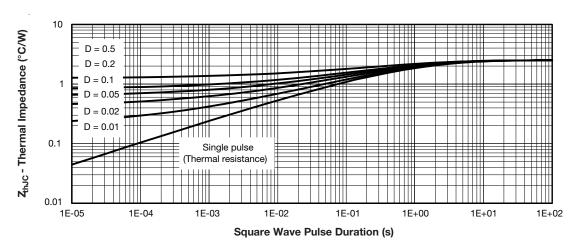


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-16TTS08FP-M3, VS-16TTS12FP-M3

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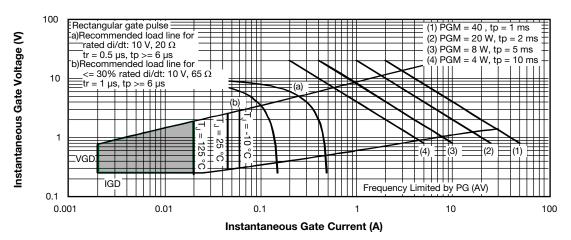
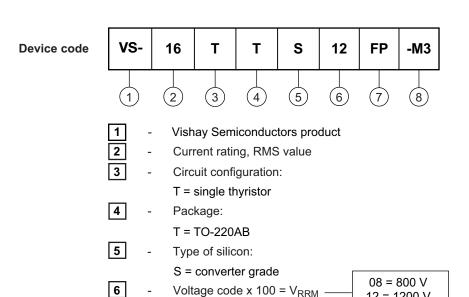


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE



FullPAK

Environmental digit: -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

12 = 1200 V

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes		
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes		

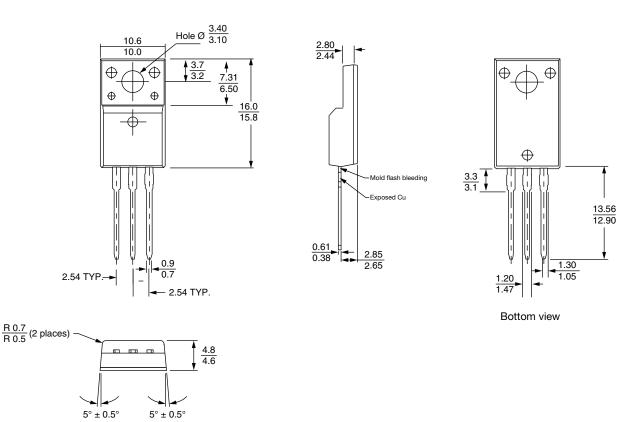
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96155</u>					
Part marking information <u>www.vishay.com/doc?95456</u>					



Vishay Semiconductors

3L TO-220 FullPAK

DIMENSIONS in millimeters



Notes

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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